

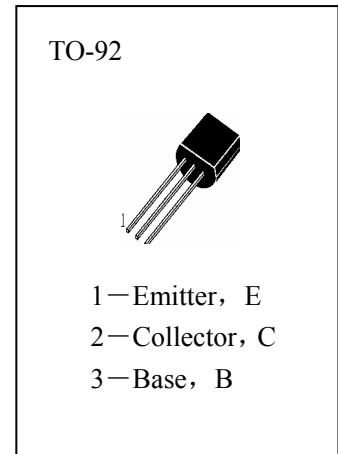


APPLICATIONS

power amplifier Applications,  
power Switching Applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

- T<sub>stg</sub>—Storage Temperature..... -55~150°C
- T<sub>j</sub>—Junction Temperature.....150°C
- P<sub>C</sub>—Collector Dissipation.....750mW
- V<sub>CBO</sub>—Collector-Base Voltage.....-50V
- V<sub>CEO</sub>—Collector-Emitter Voltage.....-50V
- V<sub>EBO</sub>—Emitter-Base Voltage.....-5V
- I<sub>C</sub>—Collector Current.....-2A



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	-50			V	I <sub>C</sub> =-100 μ A, I <sub>E</sub> =0
BVCEO	Collector-Emitter Breakdown Voltage	-50			V	I <sub>C</sub> =-10mA, I <sub>B</sub> =0
BVEBO	Emitter-Base Breakdown Voltage	-5			V	I <sub>E</sub> =-100 μ A, I <sub>C</sub> =0
ICBO	Collector Cut-off Current			-1.0	μ A	V <sub>CB</sub> =-50V, I <sub>E</sub> =0
IEBO	Emitter Cut-off Current			-1.0	μ A	V <sub>EB</sub> =-5V, I <sub>C</sub> =0
HFE(1)	DC Current Gain	70		240		V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A
HFE(2)		40				V <sub>CE</sub> =-2V, I <sub>C</sub> =-1.5A
VCE(sat)	Collector- Emitter Saturation Voltage			-0.5	V	I <sub>C</sub> =-1A, I <sub>B</sub> =-50mA
VBE(sat)	Base-Emitter Saturation Voltage			-1.2	V	I <sub>C</sub> =-1A, I <sub>B</sub> =-50mA
f <sub>T</sub>	Current Gain-Bandwidth Product		100		MHz	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A
Cob	Output Capacitance		40		pF	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz
t <sub>ON</sub>	Turn-on Time		0.1		μ S	
t <sub>STG</sub>	Storage Time		1.0		μ S	See specified test circuit
t <sub>F</sub>	Fall Time		0.1		μ S	

hFE Classification

O	Y
70—140	120—240

